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Characterization and investigation of Fe:STO thin films prepared by pulsed laser deposition

Maximilian Morgenbesser, Stefanie Taibl, Markus
Kubicek, Alexander Viernstein, Christopher Herzig,
Andreas Limbeck, Jürgen Fleig

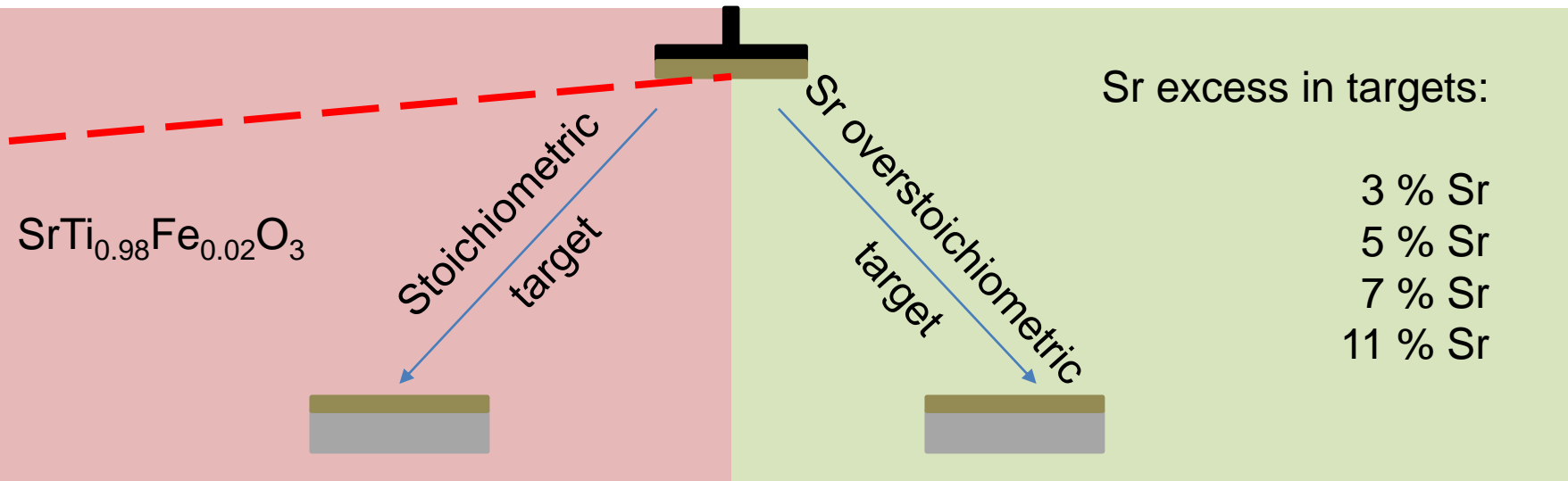
Table of content

- Introduction
- Sample preparation
- Analytical characterization
- Electrochemical characterization
- Model
- Conclusion

Introduction

- Bulk SrTiO_3 well researched, defect model well known
- Conductivity of STO can be tailored by doping
- Effect of cation nonstoichiometry on (electrical) properties not so well researched
- Aim: linking stoichiometry, structure and properties of $\text{Fe}:\text{SrTiO}_3$

Sample preparation via PLD



Deposition parameters

Standard: 400 mJ set, 650 °C,
0.15 mbar O₂; 5 Hz

Variation of laser fluence and
repetition rate for stoichiometric
targets

Substrates:

Electrical measurements: Nb:STO

XRD (reciprocal space map): STO

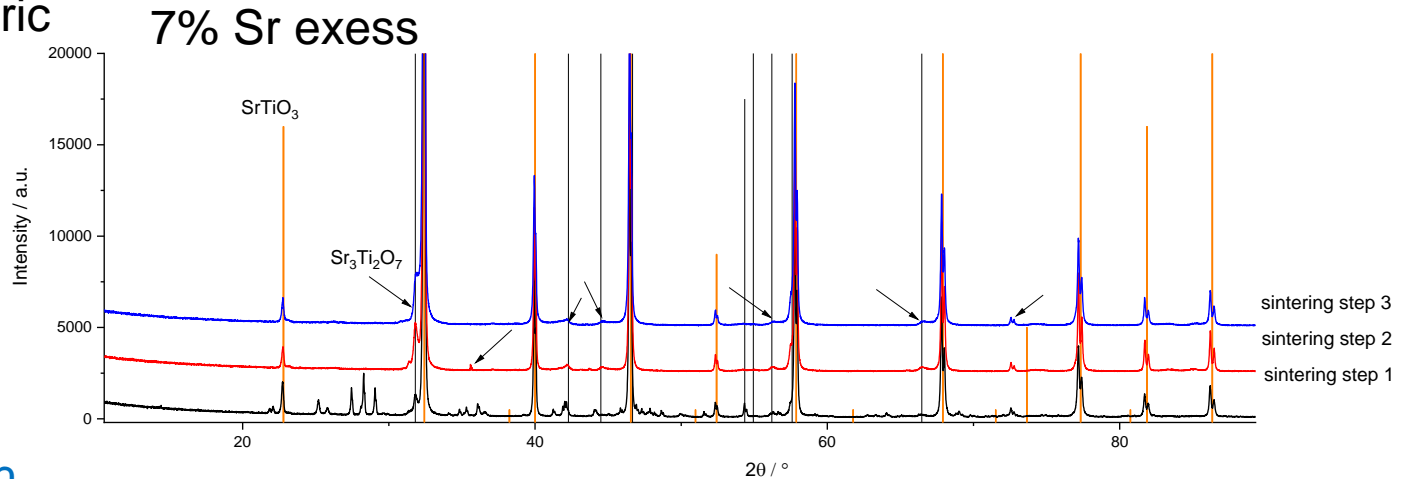
XRD (thin film gracing incidence): MgO

ICP-OES: MgO

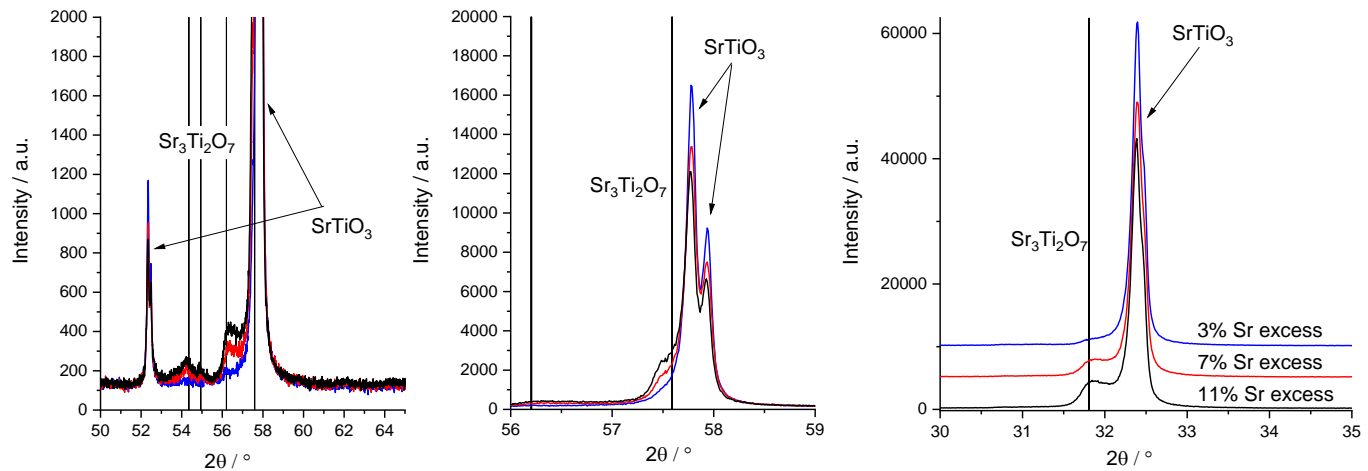
X-ray diffraction of targets

With Sr
overstoichiometry

Overstoichiometric
targets:
Solid state route
pressing, then
1) 1000 °C, 2 h
2) 1200 °C, 4 h
remilling and
pressing
3) 1400 °C, 4.5 h



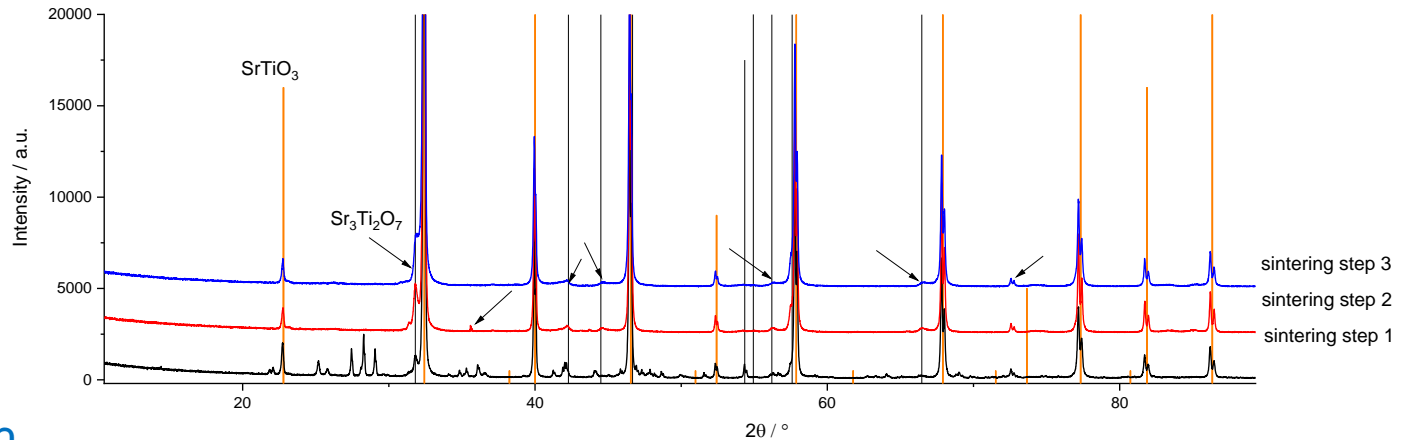
Sr-rich phases
are present
even after
three sintering
steps.



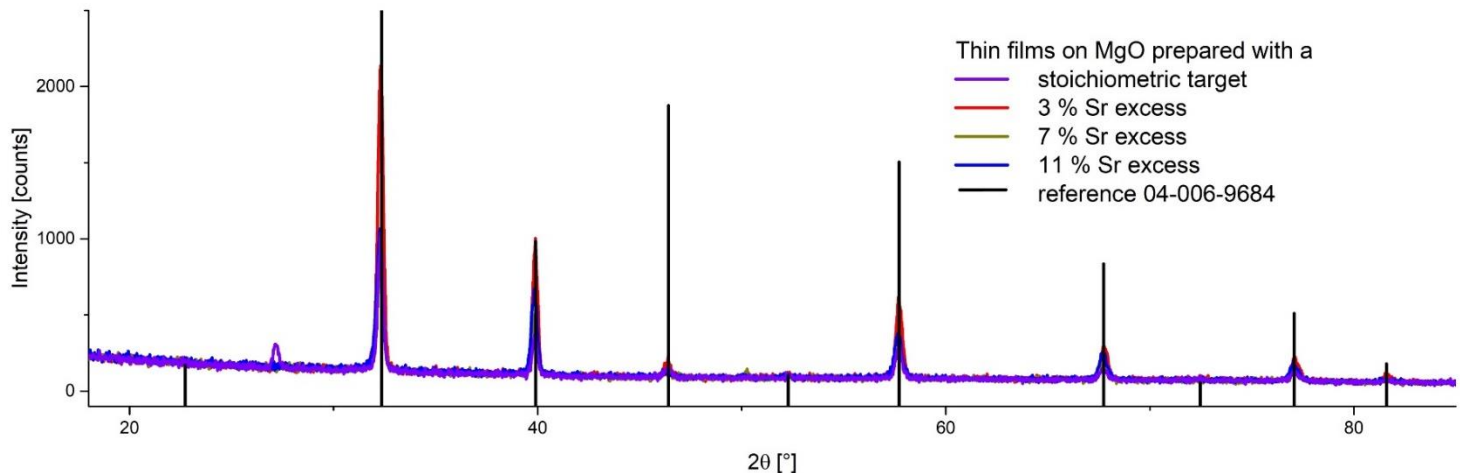
X-ray diffraction of targets

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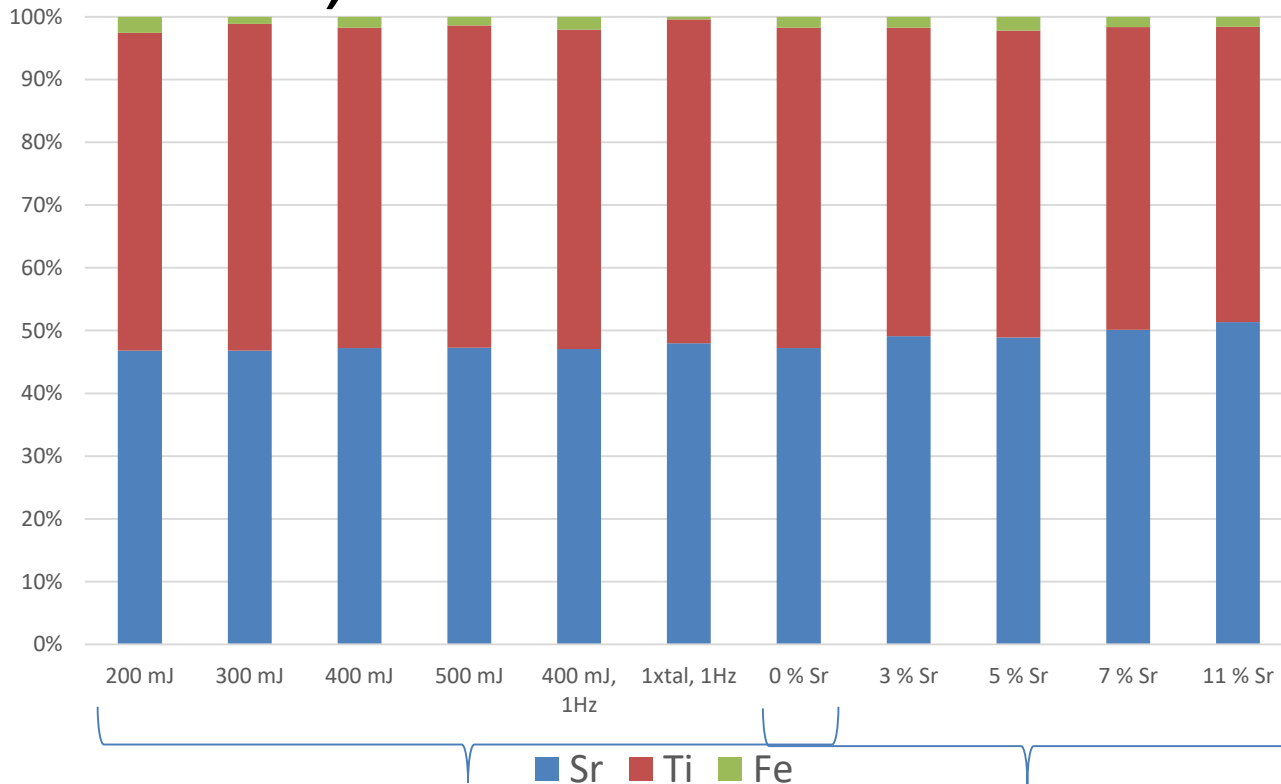
Overstoichiometric
targets:
Solid state route
pressing, then
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remilling and
pressing
3) 1400 °C, 4.5 h



Thin films are
phase pure



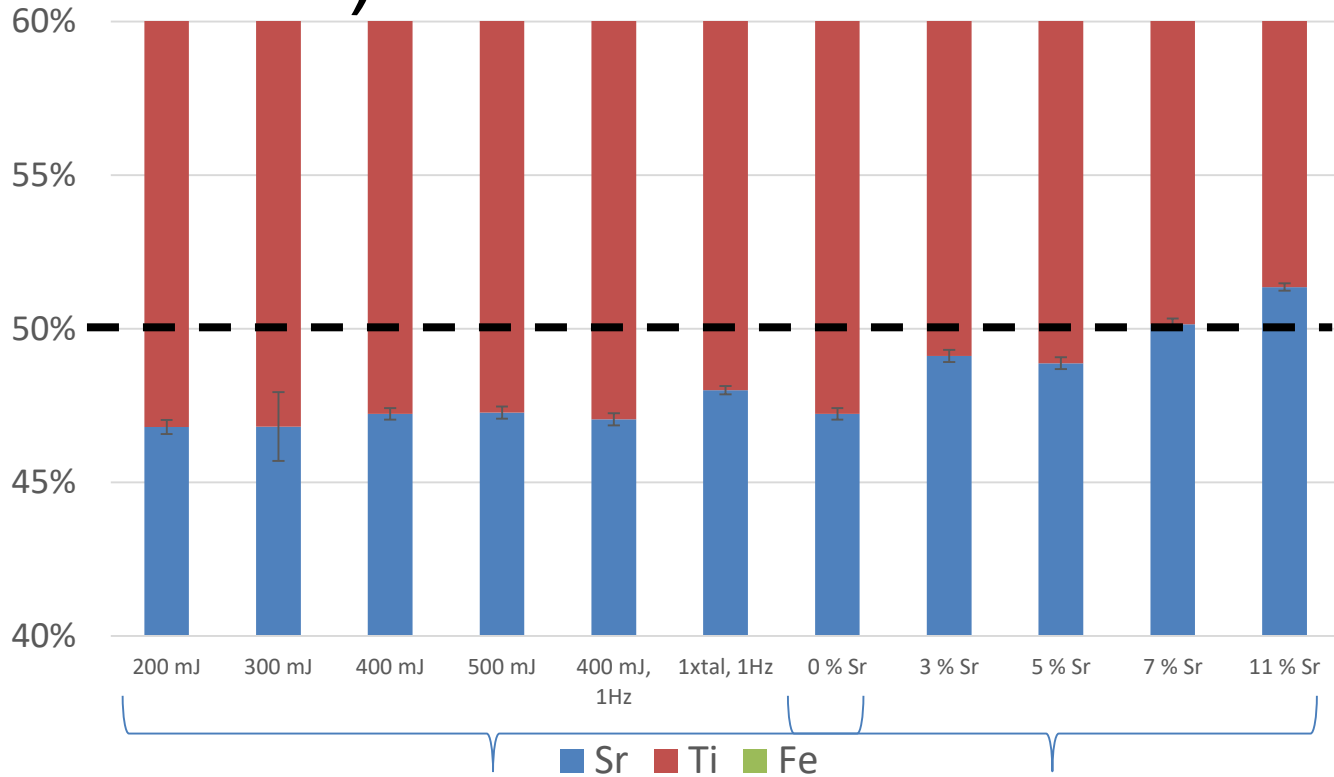
Chemical analysis of thin films (ICP-OES)



Deposited from a stoichiometric target

Sr excess in the target

Chemical analysis of thin films (ICP-OES)

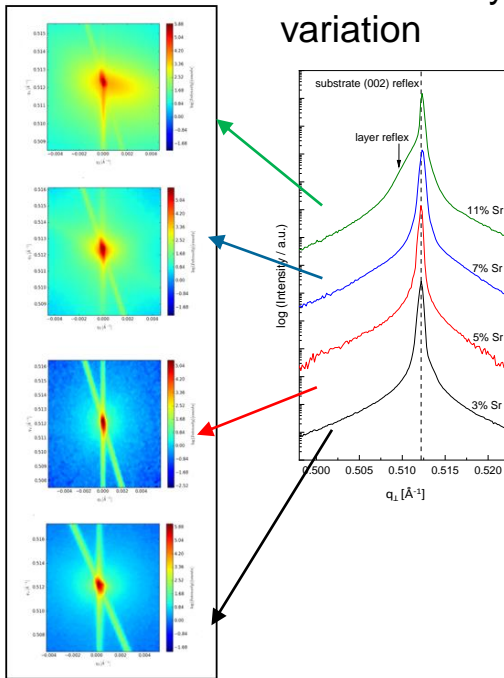


Deposited from a stoichiometric target

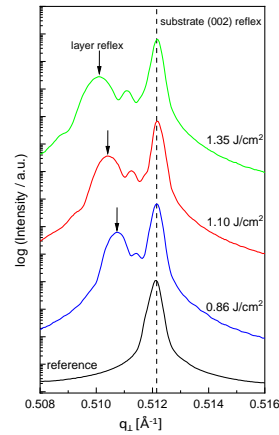
Sr excess in the target

X-ray diffraction of thin films

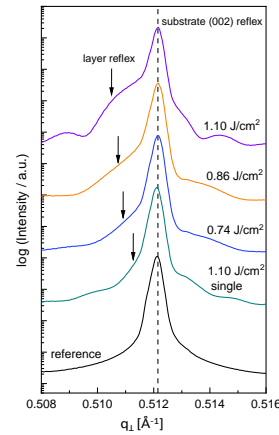
Stoichiometry variation



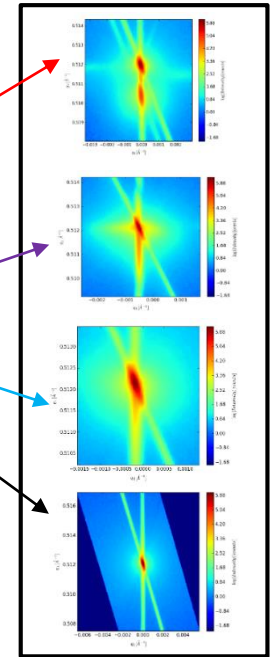
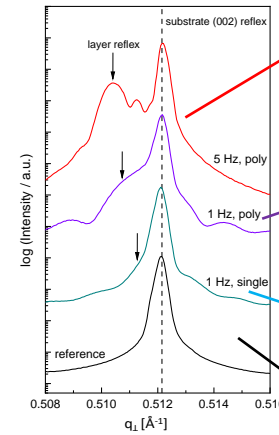
Fluence variation (5 Hz)



Fluence variation (1 Hz)



Frequency variation



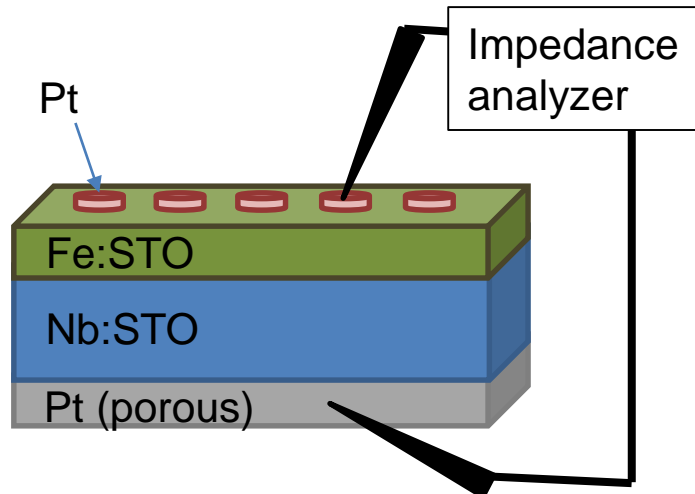
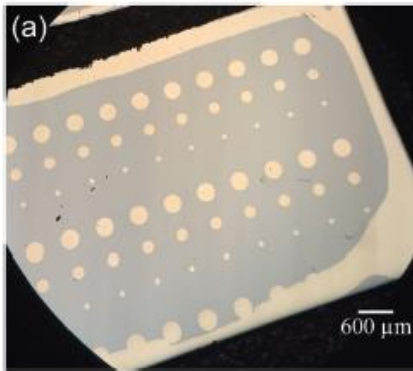
Thin films deposited on STO substrates (=reference)

Deposited from Sr overstoichiometric targets

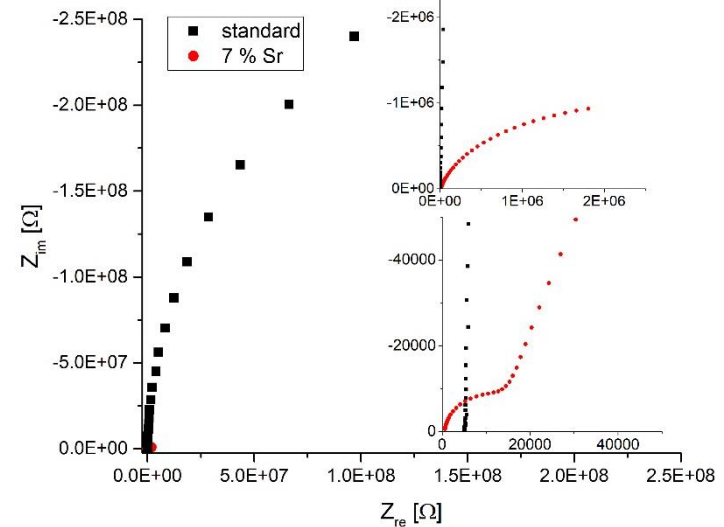
Deposited from stoichiometric targets

Conductivity measurements

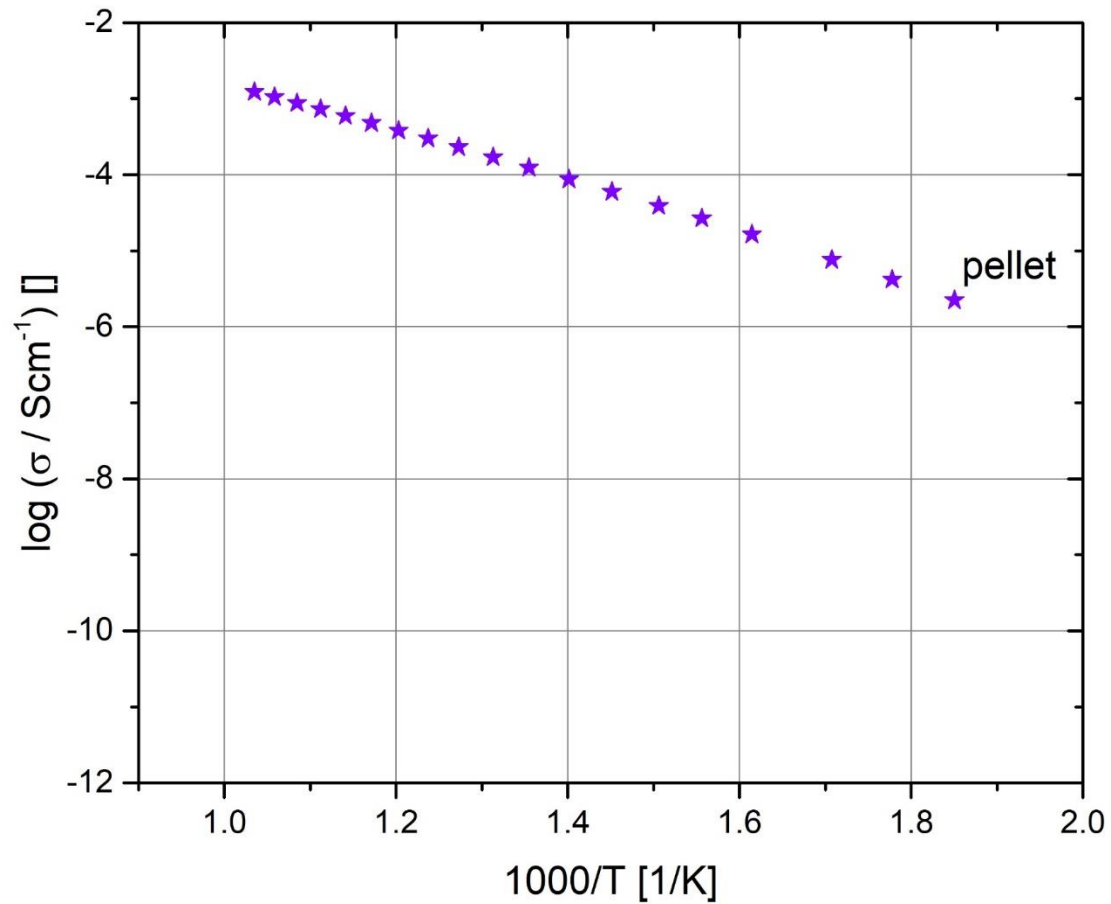
By means of Electrochemical Impedance Spectroscopy



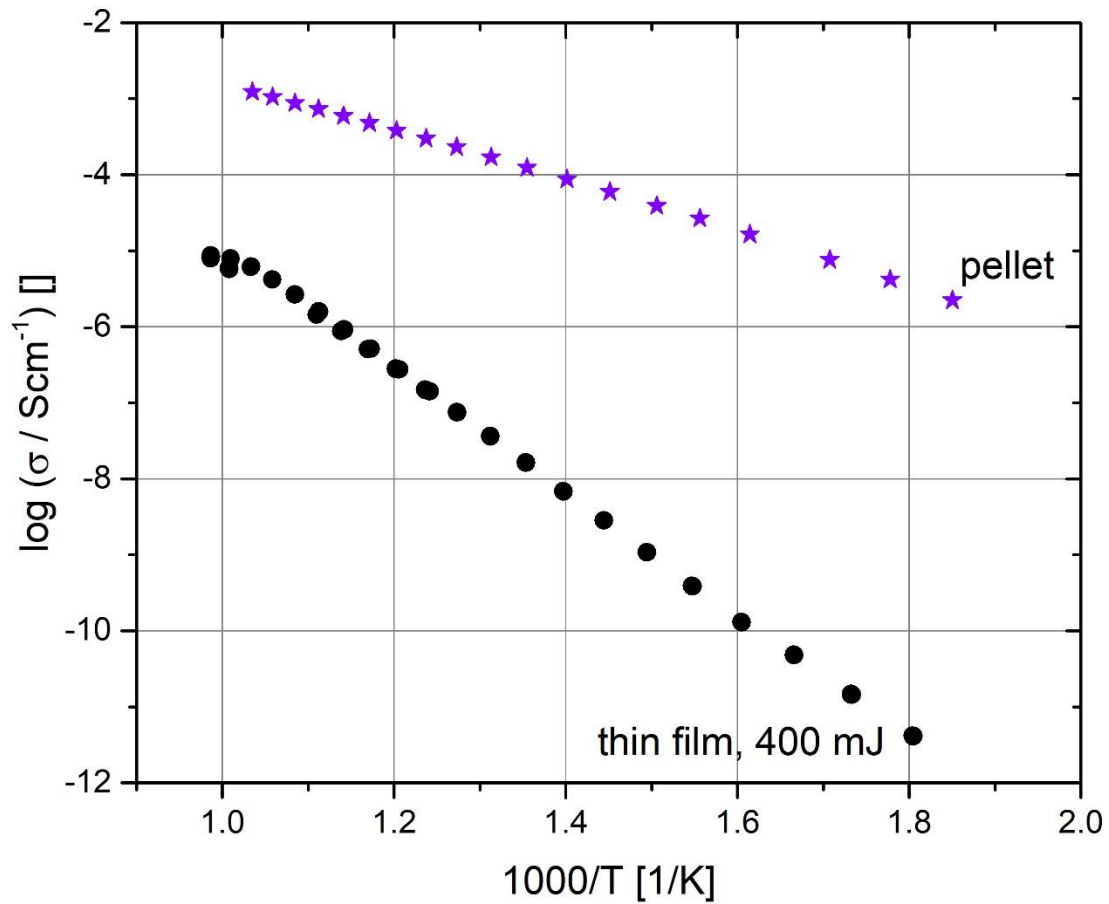
Nyquist Plot 300 °C



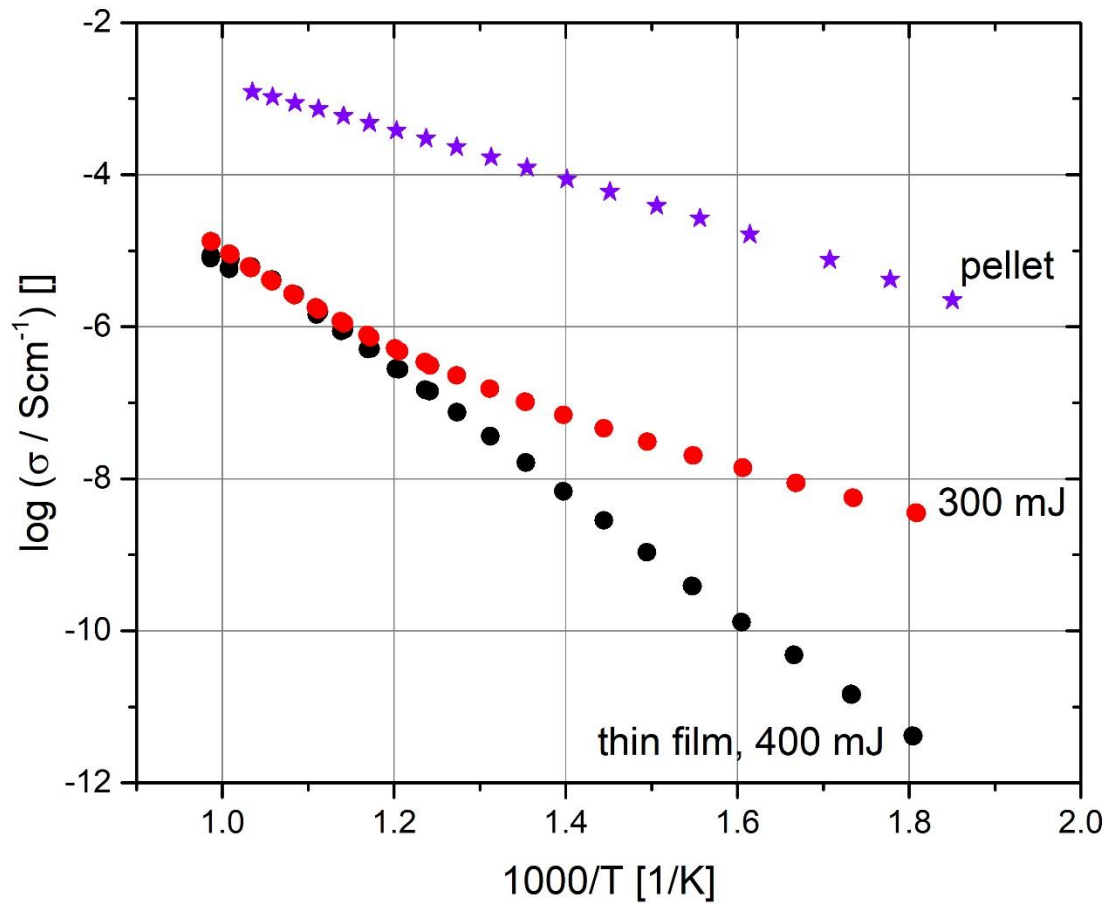
Conductivity



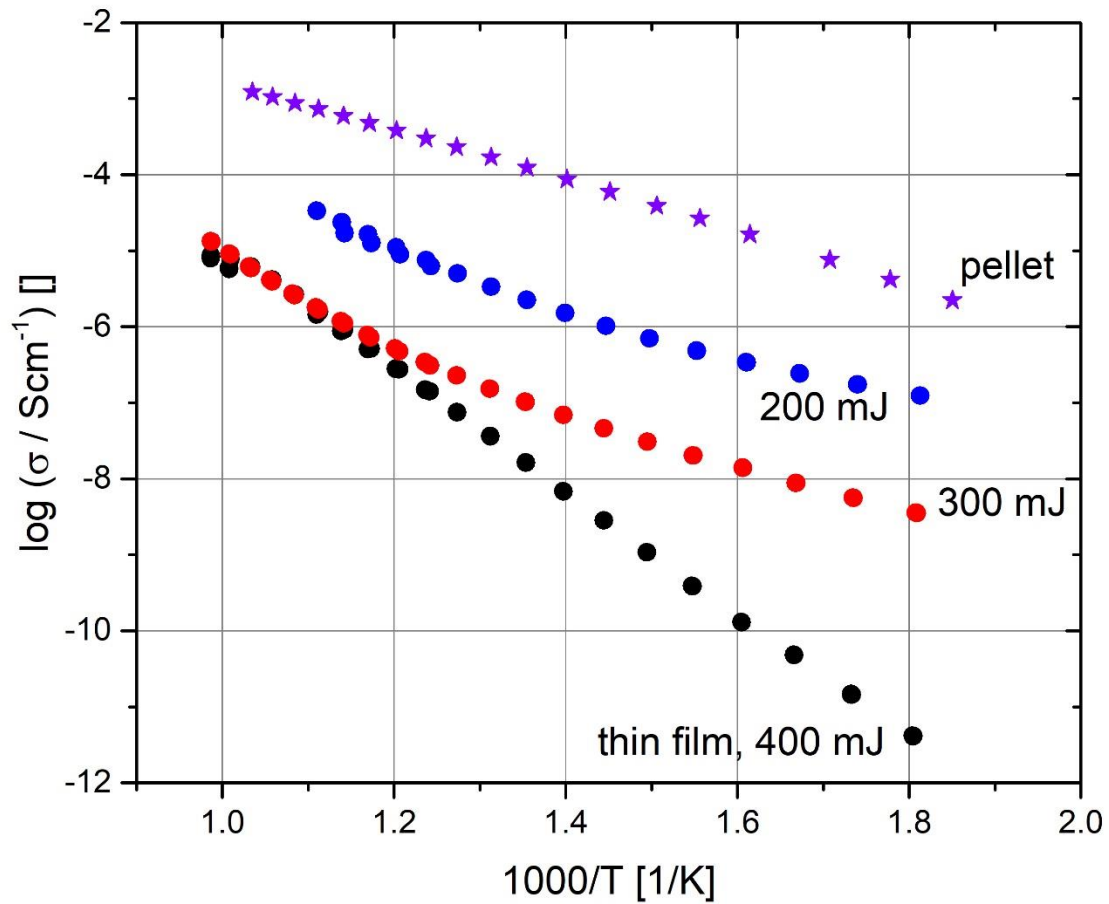
Conductivity



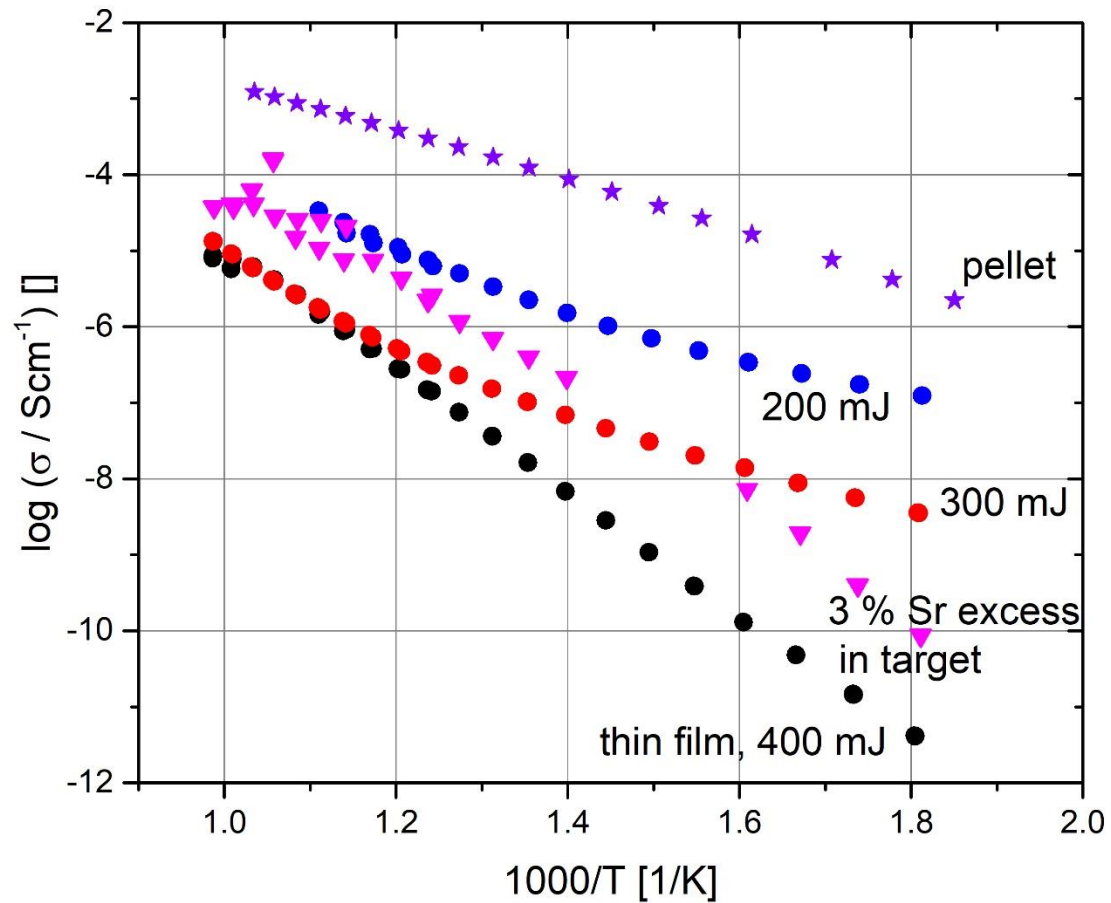
Conductivity



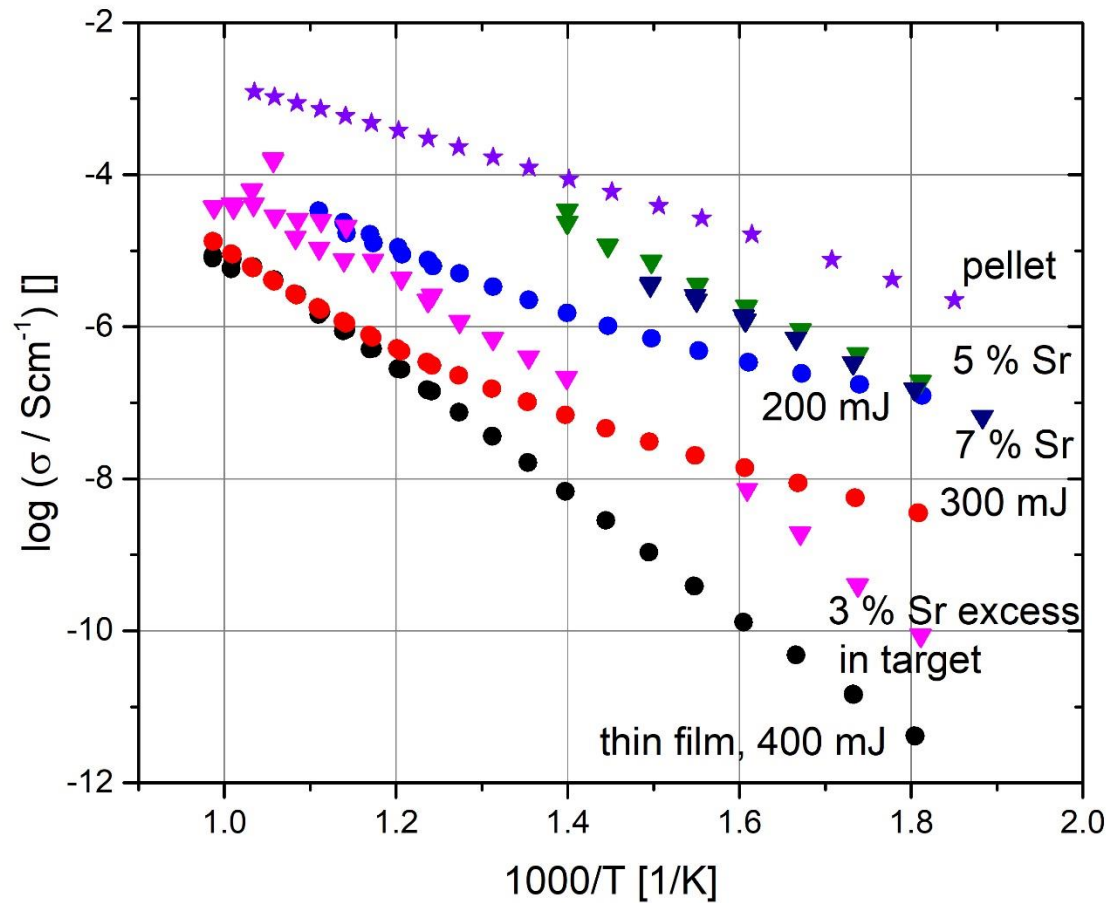
Conductivity



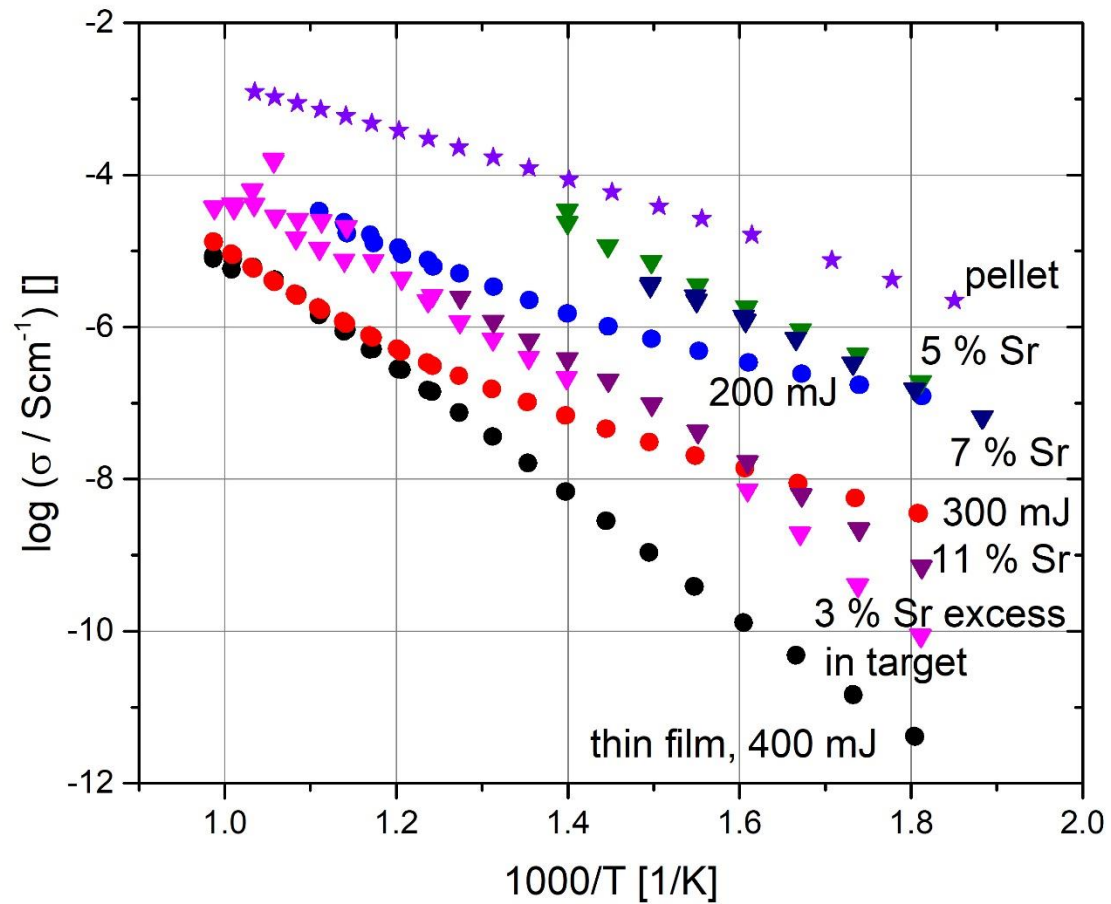
Conductivity



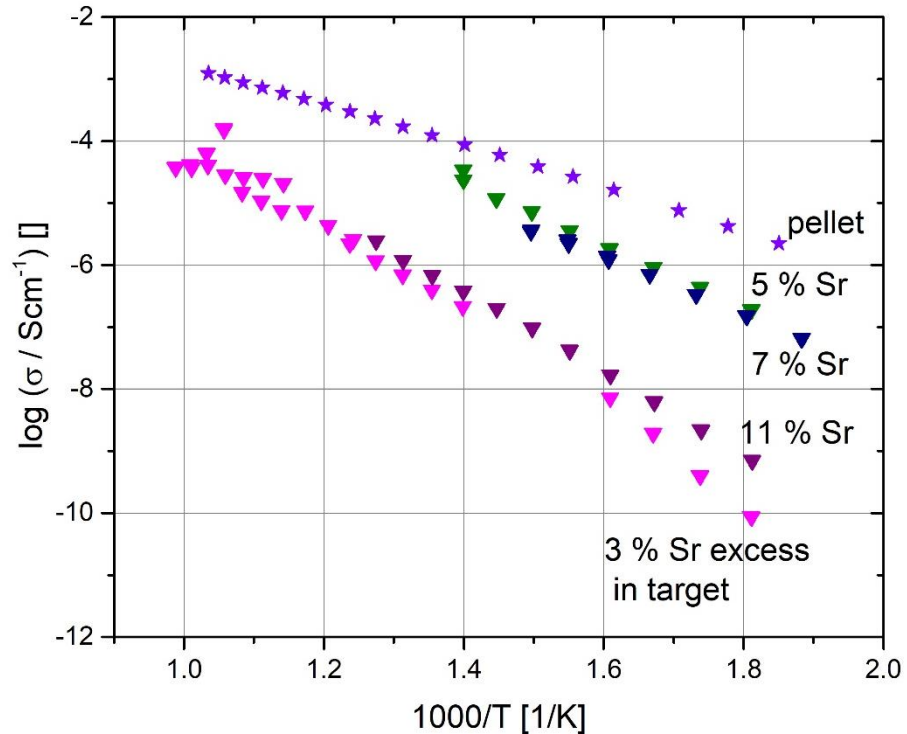
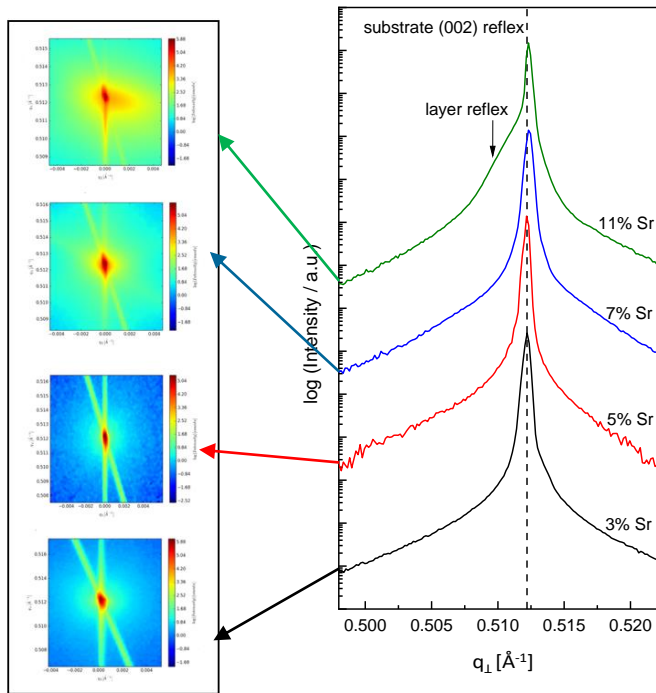
Conductivity



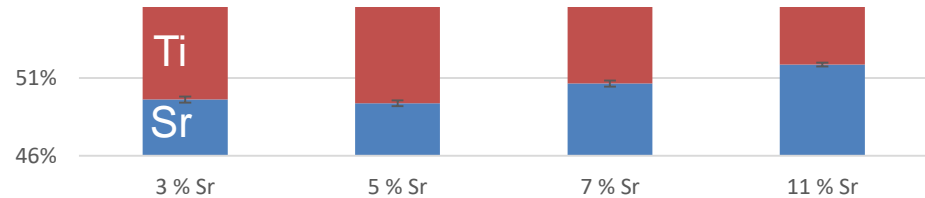
Conductivity



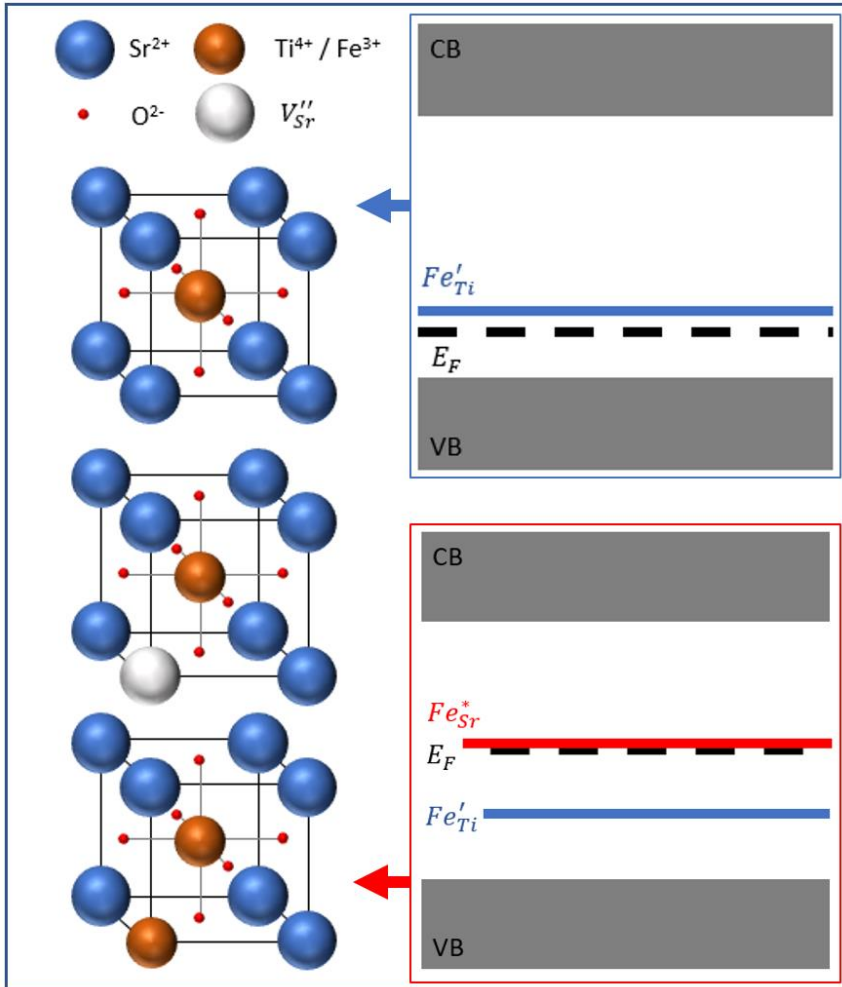
Structure vs. Conductivity



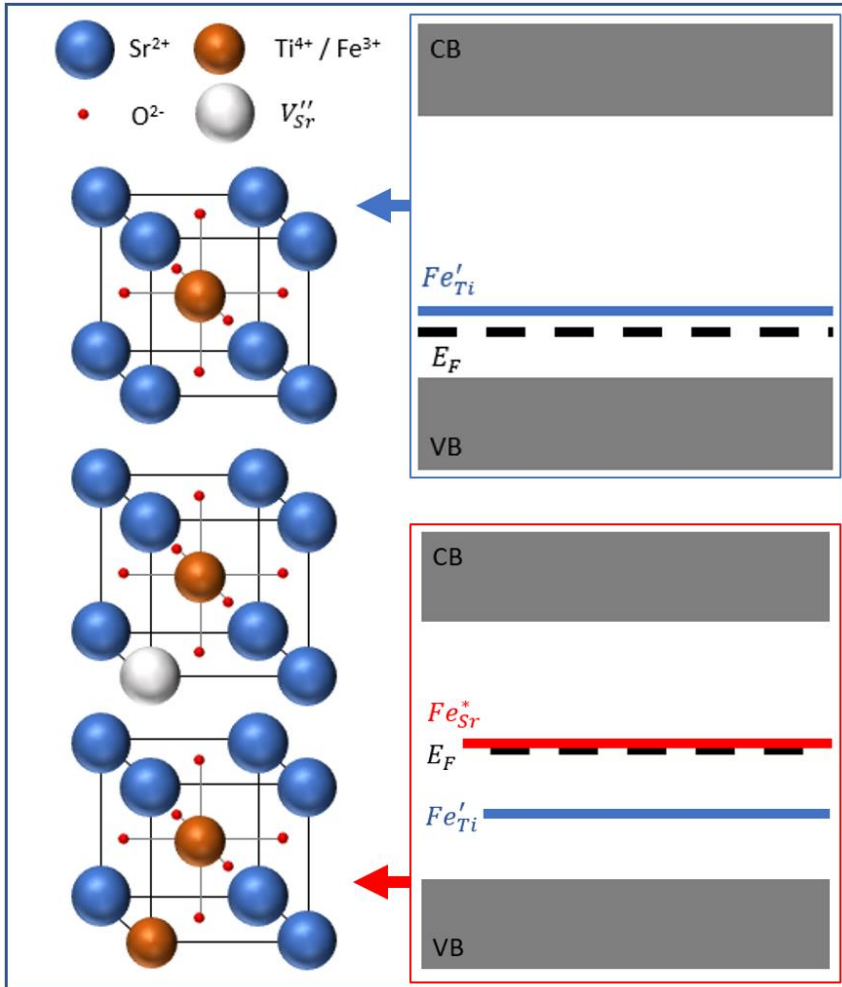
Structure and conductivity for thin films deposited from targets with a Sr overstoichiometry



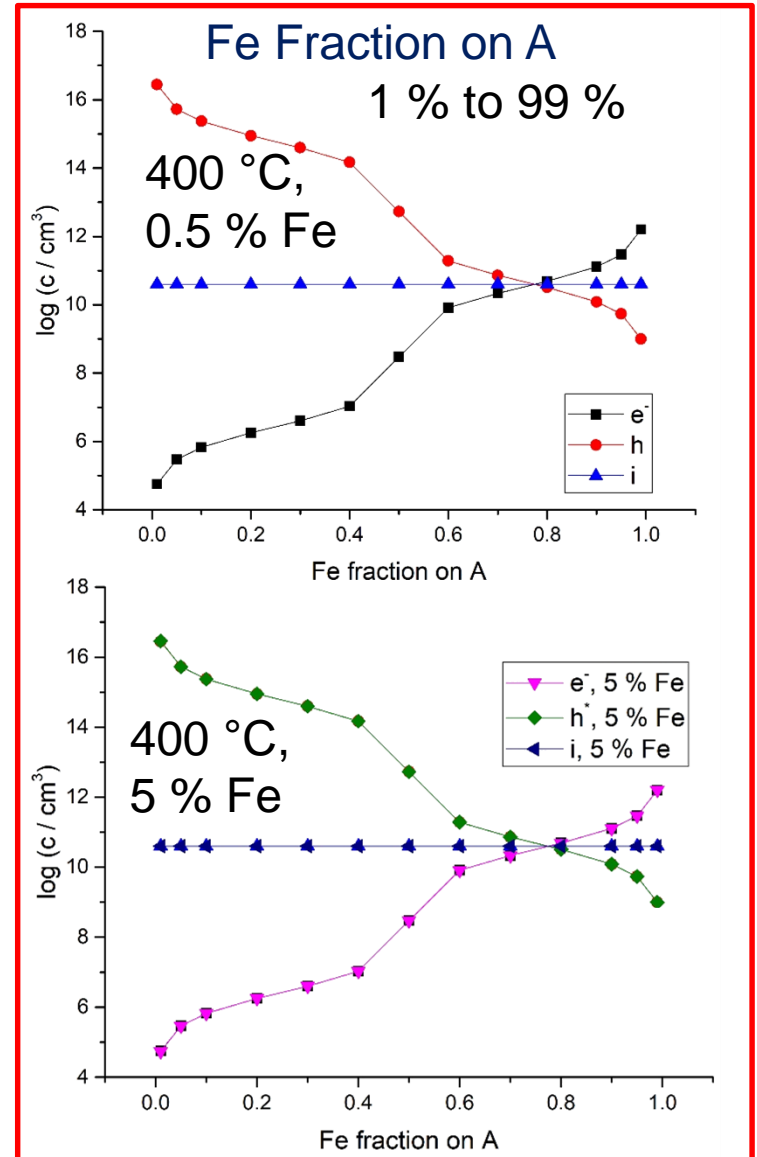
Model



Model



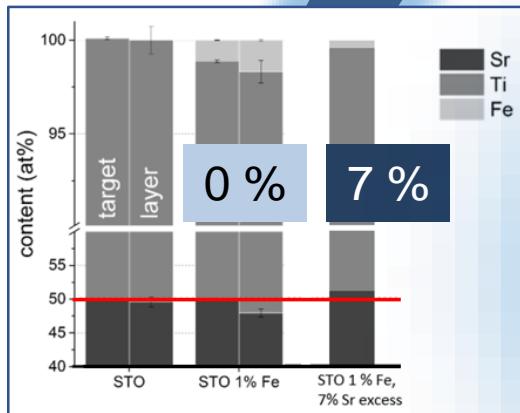
Denk, et al., J. Am. Ceram. Soc.



5. σ

Discussion

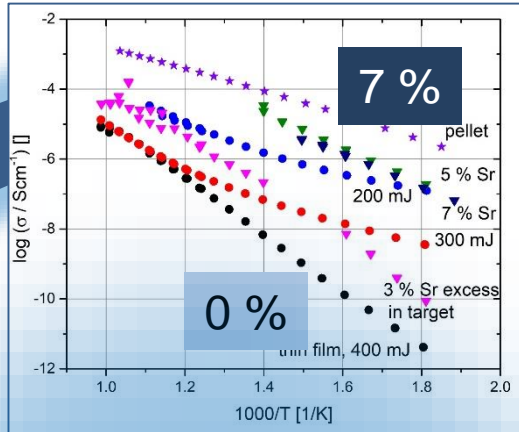
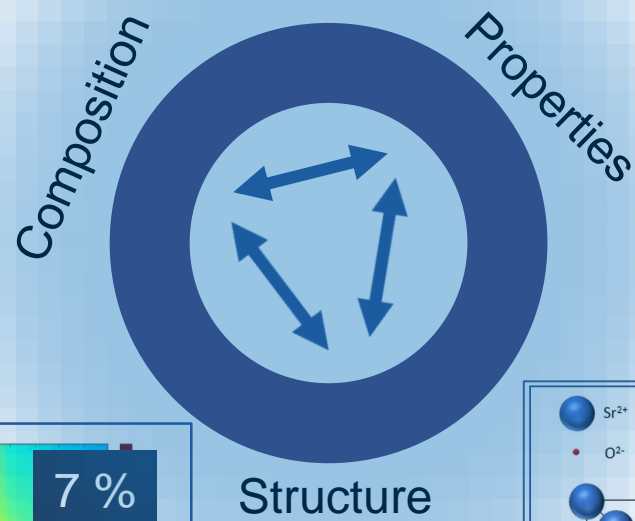
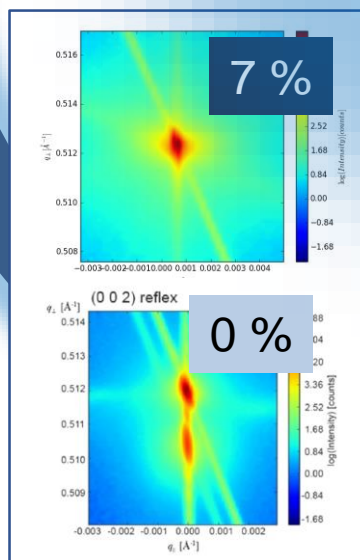
1. ICP-OES



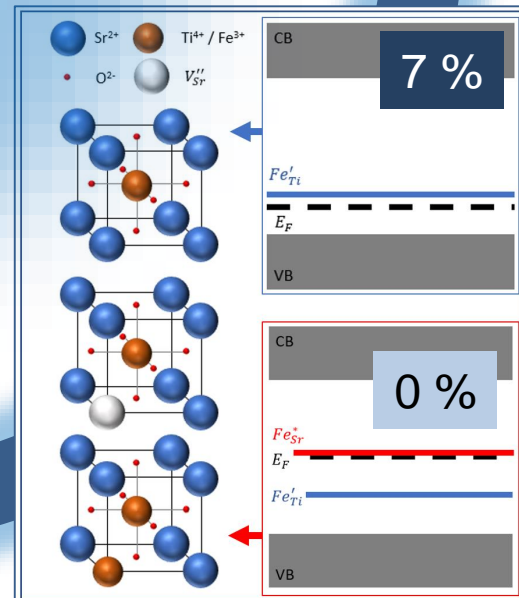
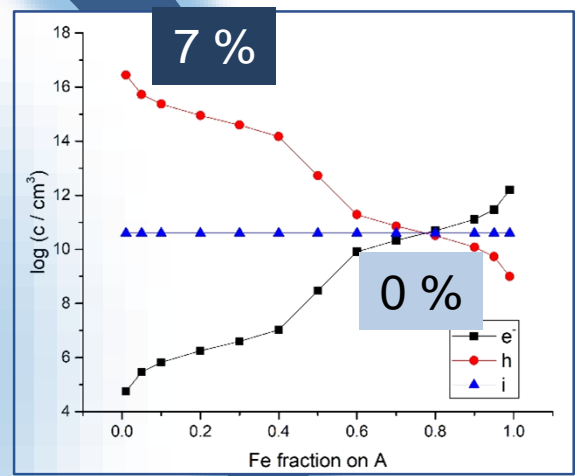
Fe:STO with Sr excess:

0 %
7 %

2. XRD



4. Charge carrier concentration



3. Band model

Thank you for your attention!



